Key Features

* Front and backside alignment capability
* Non-contact lithography
* Ability to place multiple lithography layers on a single reticle
* Off-axis MVS with focus and illumination controls
* High wafer plane irradiance
* Simple integration with existing processes
* Compact system footprint
* A proven projection lithography platform in semiconductor, thin film head and Microsystems production environments

IMAGING AND LENS

	Lens Option	
	1.0 µm	2.0 µm
Resolution	1.0 um	2.0 um
Usable Depth of Focus (at resolution limit)	> = 3.0 µm	> = 10 um
Usable Depth of Focus (4 um L/S in 10 um resist)	> = 14.0 um	> = 20.0 um
Lens Distortion (100%)	< = 160 nm	< = 350 nm
Exposure Uniformity	< = 3.0 %	< = 5.0 %
Standard Field Size	30 x 15 mm	
Wafer Plane Irradiance	> = 1000 mW/cm2	
Exposure Spectrum	390 – 450 nm Broadband	

ALIGNMENT SYSTEM

	1.0 µm	2.0 µm
MVS Alignment (site by site, 100% front side)	< = +/- 150 nm	< = +/- 250 nm
DSA Alignment (Enhanced global alignment, back side)	< = 2.0 um (3 sigma)	< = 3.0 um (3 sigma)
Alignment Spectrum	530 – 570 nm, Broadband	

THROUGHPUT **(wafers per hour at 100 mJ/cm2 , front side align)**

	1.0 µm	2.0 µm
100 mm Wafer	85 wph	85 wph
125 mm Wafer	51 wph	51 wph
150 mm Wafer	42 wph	42 wph

RETICLE

	1.0 µm	2.0 µm
Substrate Type	3 x 5 x 0.090 inch quartz	5 x 5 x 0.090 inch quartz
Fields per Reticle Row	2 – 4	2 - 4

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Specifications derived from O.E.M. published documentation, consult manufacturer for updated specification changes.